

# MMBT3904W SOT-323 Silicon General Purpose Transistor (NPN)

### **General description**

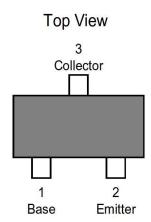
SOT-323 Silicon General Purpose Transistor (NPN)

#### **FEATURES**

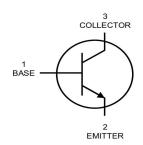
- · Simplifies Circuit Design
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- · Weight: approx. 0.001g

### **Absolute Maximum Ratings** (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Value	Units
Vсво	Collector-Base Voltage	60	V
VCEO	Collector-Emitter Voltage	40	V
VEBO	Emitter-Base Voltage	6	V
Ic	Collector Current	200	mA
P <sub>D</sub>	Power Dissipation (FR-4 Board – minimum pad)	150	mW
Reja	Thermal Resistance from Junction to Ambient	833	°C /W
Тл Тэтс	Junction & Storage Temperature Range	-55 to +150	°C



### **Electrical Symbol:**



### . Off Characteristics

Symbol	B	T	Limits	Unit	
	Parameter	Test Condition	Min	in Max	
<b>V</b> (BR)CEO	Collector-Emitter Breakdown Voltage (Note 1)	I <sub>C</sub> =1mA, I <sub>B</sub> =0A	40	-	Volts
V <sub>(BR)</sub> CBO	Collector-Base Breakdown Voltage	I <sub>C</sub> =10uA, I <sub>E</sub> =0A	60	-	Volts
V(BR)EBO	Emitter-Base Breakdown Voltage	I <sub>E</sub> =10uA, I <sub>B</sub> =0A	6	-	Volts
Івь	Base Cutoff Current	V <sub>CE</sub> =30V, V <sub>EB</sub> =3V	-	50	nA
Icex	Collector Cutoff Current	V <sub>CE</sub> =30V, V <sub>EB</sub> =3V	-	50	nA

Note 1: Pulse Test. Pulse width <300us, Duty cycle < 2.0%

# **MMBT3904W**



# On Characteristics

Oh. al	Down-ston.	Limits	nits	Unit		
Symbol	Parameter	Test Condition	Min	Max	- Volts	
		I <sub>C</sub> =0.1mA, V <sub>CE</sub> =1V	40	-		
		I <sub>C</sub> =1.0mA, V <sub>CE</sub> =1V	70	-		
H <sub>FE</sub>	DC Current Dain	I <sub>C</sub> =10mA, V <sub>CE</sub> =1V	100	300	-	
		I <sub>C</sub> =50mA, V <sub>CE</sub> =1V	60	_		
		I <sub>C</sub> =100mA, V <sub>CE</sub> =1V	30	-		
	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA	-	0.2		
VCE(sat)		I <sub>C</sub> =50mA, I <sub>B</sub> =5mA	_	0.3	Volts	
	Base-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA	0.65	0.85		
V <sub>BE(sat)</sub>		I <sub>C</sub> =50mA, I <sub>B</sub> =5mA	-	0.95	Volts	

**Small-signal Characteristics** 

Symbol	Parameter	Test Condition	Limits		Unit
	Faranieter	rest Condition	Min	Max	Offic
f⊤	Current-Gain-Bandwidth Product	I <sub>C</sub> =10mA, V <sub>CE</sub> =20V, f = 100MHz	200	-	MHz
Cobo	Output Capacitance	V <sub>CB</sub> =5V, I <sub>E</sub> =0A, f = 1.0MHz	-	4	pF
Cibo	Input Capacitance	V <sub>BE</sub> =0.5V, I <sub>C</sub> =0A, f = 1.0MHz	-	8	pF
h <sub>ie</sub>	Input Impedancen	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA, f = 1.0kHz	1	10	pF
h <sub>re</sub>	Voltage Feedback Ratio	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA, f = 1.0kHz	0.5	8	X10 <sup>-4</sup>
h <sub>fe</sub>	Small-signal Current Gain	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA, f = 1.0kHz	100	400	-
h <sub>oe</sub>	Output Admittance	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA, f = 1.0kHz	1	40	θ mhos
NF	Noise Figure	V <sub>CE</sub> =5V, I <sub>C</sub> =100uA		5	dB
	11000 Figuro	Rs=1.0k $\Omega$ f = 1.0kHz			u.b

### **Switching Characteristics**

O. mala al	Downston	To at O an dition	Limits		11:4	
Symbol	Parameter	Test Condition	Min	Max	Unit	
<b>t</b> d	Delay Time	V <sub>CC</sub> =3V, V <sub>BE</sub> =0.5V,	-	35	20	
<b>t</b> r	Rise Time	I <sub>C</sub> =10mA, I <sub>B1</sub> =1mA	-	35	nS	
<b>t</b> s	Storage Time	Vcc = 3V, Ic = 10mA,	-	200	20	
<b>t</b> f	Fall Time	I <sub>B1</sub> = I <sub>B2</sub> =1mA	-	50	nS	



# **Typical characteristics**

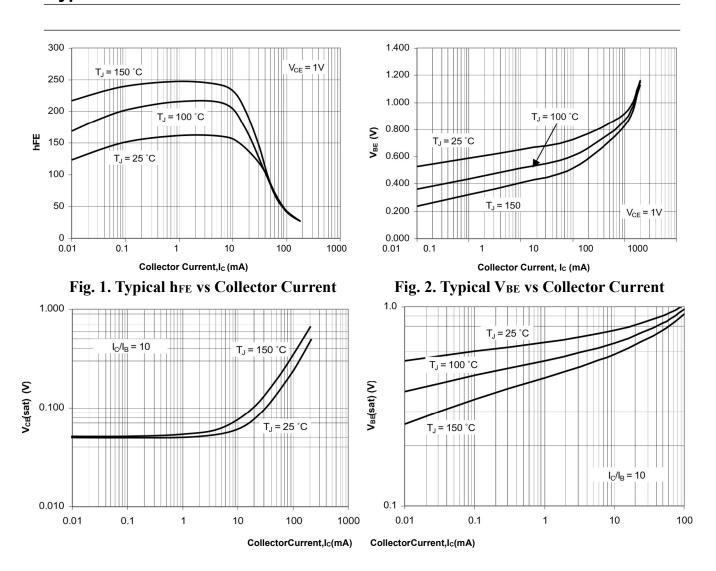


Fig. 3. Typical VCE (sat) vs Collector Current Fig. 4. Typical VBE (sat) vs Collector Current

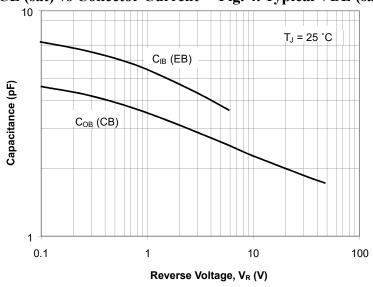
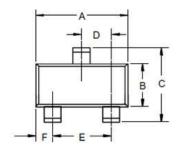
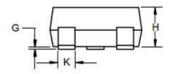


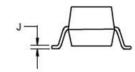
Fig. 5. Typical Capacitances vs Reverse Voltage



# **SOT-323 Package information**

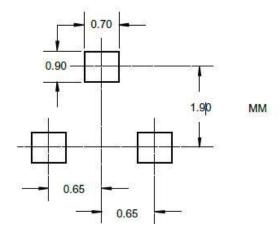






		DIMEN	ISIONS		
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
Α	.071	.087	1.80	2.20	
В	.045	.053	1.15	1.35	
C	.083	.096	2.10	2.45	7.
D	.026 Nominal		0.65Nominal		C.
Е	.047	.055	1.20	1.40	00
F	.012	.016	.30	.40	13
G	.000	.004	.000	.100	
Н	.035	.039	.90	1.00	
J	.004	.010	.100	.250	7.
K	.006	.016	.15	.40	

# **Suggested Pad Layout**





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